

IRF3711Z Information

Part Number IRF3711Z

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 20V 92A TO-220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

Website: https://www.heisener.com

E-mail: salesdept@heisener.com



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IRF3711Z Specifications

Manufacturer Part Number IRF3711Z Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 92A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.45V @ 250µA Gate Charge (Qg) (Max) @ Vgs 24nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 2150pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 79W (Tc) Rds On (Max) @ Id, Vgs 6 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3 Report errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 92A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.45 V @ 250μA Gate Charge (Qg) (Max) @ Vgs 24nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 2150pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 79W (Tc) Rds On (Max) @ Id, Vgs 6 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220AB	Manufacturer Part Number	IRF3711Z
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Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Prive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) **Euror** **Euror** **Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature **One Mounting Type **Through Hole Supplier Device Package Package / Case **MOSFET (Metal Oxide) **20V **Supplier Device Package **MOSFET (Metal Oxide) **20V **PET (Metal Oxide) **20V **PET (Metal Oxide) **20V **PET (Power Oside) **One (Associated) **One (Associated) **One (Associated) **One (Associated) **Through Hole **To-220AB **To-220AB **To-220-3	Series	HEXFET?
Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C92A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.45V @ 250μAGate Charge (Qg) (Max) @ Vgs24nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds2150pF @ 10VVgs (Max)±20VFET Feature-Power Dissipation (Max)79W (Tc)Rds On (Max) @ Id, Vgs6 mOhm @ 15A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature For Cate Charge (Qg) (Max) @ Vds To-220AB Package / Case Power Dissipation (Id) @ 25°C 92A (Tc) 9	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.45V @ 250μAGate Charge (Qg) (Max) @ Vgs24nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds2150pF @ 10VVgs (Max)±20VFET Feature-Power Dissipation (Max)79W (Tc)Rds On (Max) @ Id, Vgs6 mOhm @ 15A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Drain to Source Voltage (Vdss)	20V
Vgs(th) (Max) @ Id 2.45 V @ 250μA Gate Charge (Qg) (Max) @ Vgs 24nC @ 4.5 V Input Capacitance (Ciss) (Max) @ Vds 2150pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 79W (Tc) Rds On (Max) @ Id, Vgs 6 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Current - Continuous Drain (Id) @ 25°C	92A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 2150pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 6 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 6 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs(th) (Max) @ Id	2.45V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)79W (Tc)Rds On (Max) @ Id, Vgs6 mOhm @ 15A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	24nC @ 4.5V
FET Feature - Power Dissipation (Max) 79W (Tc) Rds On (Max) @ Id, Vgs 6 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	2150pF @ 10V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 6 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs6 mOhm @ 15A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Power Dissipation (Max)	79W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	6 mOhm @ 15A, 10V
Supplier Device Package TO-220AB Package / Case TO-220-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
•	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

IRF3711Z Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRF3711Z Payment Methods





















IRF3711Z Shipping Methods













If you have any question about IRF3711Z, please do not hesitate to contact us!

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